LISTING OF CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A PMOS device having a drain junction breakdown point and a maximum impact ionization point, and including:

a gate;

a body; and

an extended drain region formed in the body, wherein the extended drain region includes a drain, a deep drain implant, and a lightly doped drain implant between the deep drain implant and the gate, at least a portion of the lightly doped drain implant is located between the drain and the gate, at least a portion of the deep drain implant is located below the drain, and ~~at least one of the drain junction breakdown point and~~ the maximum impact ionization point is located below the lightly doped drain implant within at least one of the body and the extended drain region so as to reduce any drain breakdown voltage walk-in exhibited by the device below a predetermined value.

2. (original) The PMOS device of claim 1, wherein both the drain junction breakdown point and the maximum impact ionization point are located sufficiently far from the gate that the device exhibits no significant drain breakdown voltage walk-in.

3. (original) The PMOS device of claim 2, wherein both the drain junction breakdown point and the maximum impact ionization point are located sufficiently far from the gate that any drain breakdown voltage walk-in exhibited by the device has absolute magnitude not greater than two volts.

4. (previously presented) The PMOS device of claim 1, wherein the PMOS device is a high voltage power transistor.

5. (original) The PMOS device of claim 4, wherein both the drain junction breakdown point and the maximum impact ionization point are located sufficiently far from the gate that the device exhibits no significant drain breakdown voltage walk-in.

6. (original) The PMOS device of claim 4, wherein both the drain junction breakdown point and the maximum impact ionization point have been located sufficiently far from the gate to reduce any drain breakdown voltage walk-in exhibited by the device below the predetermined value, by controlling an implant dose employed to produce the lightly doped drain implant.

7. (original) The PMOS device of claim 6, wherein the device has been manufactured in accordance with a BiCMOS process, and the implant dose is much less than $2.23 \times 10^{12}$ ions/$cm^2$ .

8. (original) The PMOS device of claim 7, wherein the implant dose is at least substantially equal to $1.15 \times 10^{12}$ ions/$cm^2$.

9. (canceled)

10. (original) The PMOS device of claim 1, wherein the maximum impact ionization point is located sufficiently far from the gate to reduce any drain breakdown voltage walk-in exhibited by the device below the predetermined value.

11. (canceled)

12. (canceled)

13. (canceled)

14. (canceled)

15. (canceled)

16. (canceled)

17. (canceled)

18. (canceled)

19. (canceled)

20. (canceled)

21. (canceled)

22. (canceled)

23. (canceled)

24. (canceled)

25. (canceled)

26. (canceled)

27. (canceled)

28. (canceled)

29. (canceled)

30. (canceled)

31. (canceled)

32. (previously presented) A PMOS device having a drain junction breakdown point and a maximum impact ionization point, and including:

a gate;

a body; and

an extended drain region formed in the body, wherein the extended drain region includes a drain, a deep drain implant, and a lightly doped drain implant between the deep drain implant and the gate, at least a portion of the lightly doped drain implant is located between the drain and the gate, at least a portion of the deep drain implant is located below the drain, and at least one of the drain junction breakdown point and the maximum impact ionization point is located within at least one of the body and the extended drain region so as to reduce any drain breakdown voltage walk-in exhibited by the device below a predetermined value, wherein at least one of the drain junction breakdown point and the maximum impact ionization point is located below the lightly doped drain implant.

33. (previously presented) The PMOS device of claim 32, wherein said at least one of the drain junction breakdown point and the maximum impact ionization point is located within at least one of the body and the deep drain implant.

Add the following new claims:

34. (new) The PMOS device of claim 32, wherein said device also includes gate oxide between the gate and the body, and wherein the maximum impact ionization point and the

drain junction breakdown point are located sufficiently far from the gate to prevent hot carrier ionization in the extended drain region and the body during stressed operation of the device from causing significant charge injection to the gate oxide during said stressed operation.

35. (new) The PMOS device of claim 34, wherein said device also includes a source, and said stressed operation of the device is operation with a voltage substantially equal to 80 volts between the source and the drain.

36. (new) The PMOS device of claim 2, wherein said device also includes gate oxide between the gate and the body, and wherein the maximum impact ionization point and the drain junction breakdown point are located sufficiently far from the gate to prevent hot carrier ionization in the extended drain region and the body during stressed operation of the device from causing significant charge injection to the gate oxide during said stressed operation.

37. (new) The PMOS device of claim 36, wherein said device also includes a source, and said stressed operation of the device is operation with a voltage substantially equal to 80 volts between the source and the drain.